

30V N-Channel Enhancement Mode MOSFET

Description

The NP3095G uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- ◆ $V_{DS} = 30V$, $I_D = 95A$
 $R_{DS(ON)}(Typ.) = 4.3m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)}(Typ.) = 6.9m\Omega @ V_{GS} = 4.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

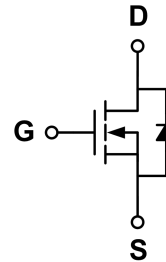
- ◆ Load switch

Package

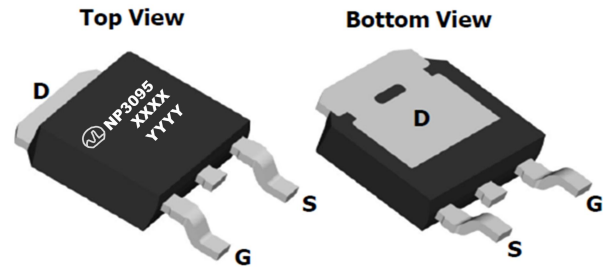
- ◆ TO-252-2L



Schematic diagram



Marking and pin assignment



XXXX—Wafer Information
 YYYY—Quality Code

Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
NP3095G-G	-55°C to +150°C	TO-252-2L	2500

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit	
Drain-source voltage	V_{DS}	30	V	
Gate-source voltage	V_{GS}	±20	V	
Continuous Drain Current	I_D	TC=25°C	95	A
		TC=70°C	66	
Pulsed Drain Current	I_{DP}	380	A	
Avalanche energy(L=0.5mH)	EAS	231	mJ	
Maximum power dissipation	P_D	TC=25°C	20	W
		TC=70°C	9	
Operating junction Temperature range	T_j	-55—150	°C	

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
		$T_J=85^\circ C$	-	-	30	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Drain-source on-state resistance ¹	$R_{DS(on)}$	$V_{GS}=10V, I_D=1A$	-	4.3	5.5	$m\Omega$
		$V_{GS}=4.5V, I_D=1A$	-	6.9	8.5	$m\Omega$
On Status Drain Current	$I_{D(on)}$	$V_{DS}=10V, V_{GS}=10V$	95	-	-	A
Diode Characteristics						
Diode Continuous Forward Current	I_S		-	95	-	A
Reverse Recovery Time	t_{rr}	$I_F=20A,$	-	34	-	ns
Reverse Recovery Charge	Q_{rr}	$dI/dt=100A/\mu s$	-	30	-	nC
Dynamic Characteristics²						
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	1.5	-	Ω
Input capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=15V$ $f=1.0MHz$	-	2153	-	pF
Output capacitance	C_{OSS}		-	289	-	
Reverse transfer capacitance	C_{RSS}		-	238	-	
Turn-on delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V,$ $R_L=20\Omega, I_D=1A, R_G=6\Omega$	-	13	-	ns
Turn-on Rise time	t_r		-	14	-	
Turn-off delay time	$t_{D(off)}$		-	38	-	
Turn-off Fall time	t_f		-	16	-	
Total gate charge	Q_g	$V_{GS}=10V, I_D=1A$ $V_{DS}=15V$	-	46.3	-	nC
Gate-source charge	Q_{gs}		-	39.7	-	
Gate-drain charge	Q_{gd}		-	1	-	
Drain-Source Diode Characteristics						
Diode forward voltage	V_{SD}	$I_{SD}=1A, V_{GS}=0V$	-	0.7	1.2	V

Note: 1: Pulse test; pulse width $\leq 300ns$, duty cycle $\leq 2\%$.

2: Guaranteed by design, not subject to production testing.

Typical Performance Characteristics

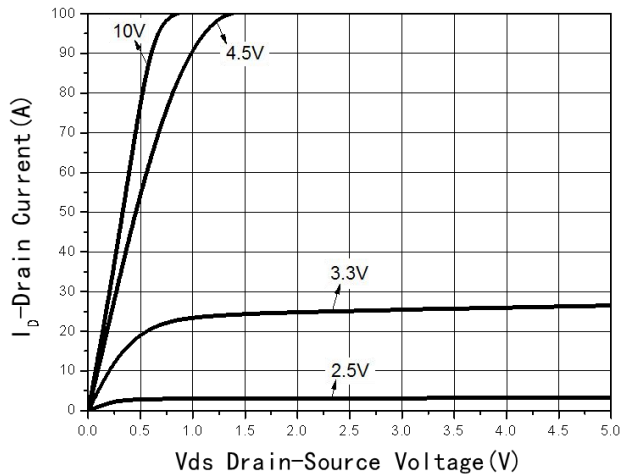


Fig1 Output Characteristics

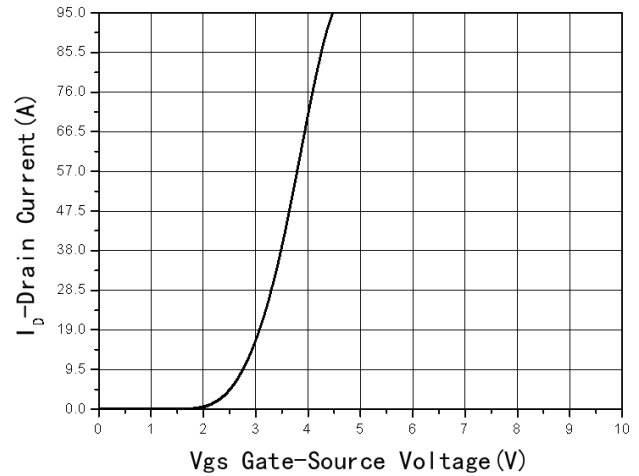


Fig2 Transfer Characteristics

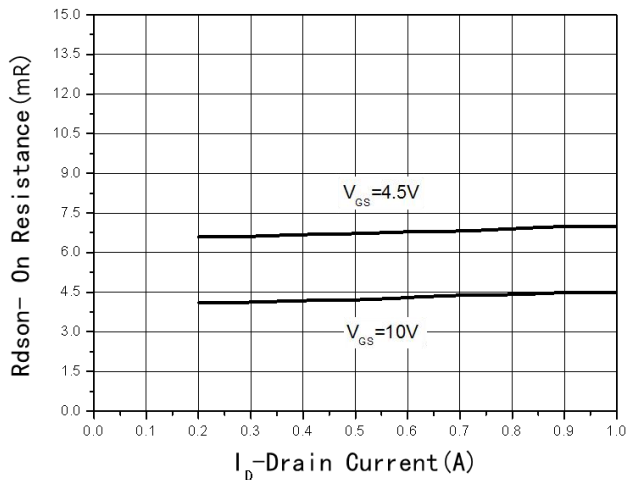


Fig3 Rds(on)-Drain current

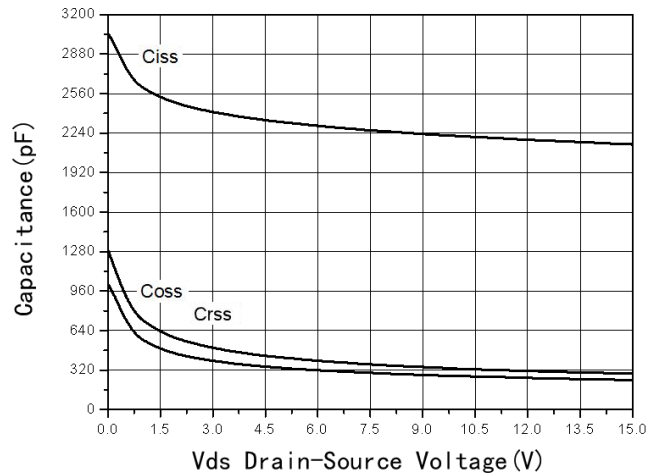


Fig4 Capacitance vs Vds

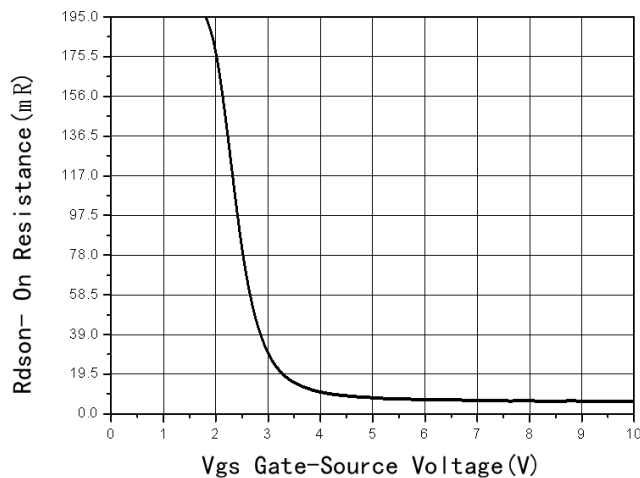


Fig5 Rds(on)-Gate Drain voltage

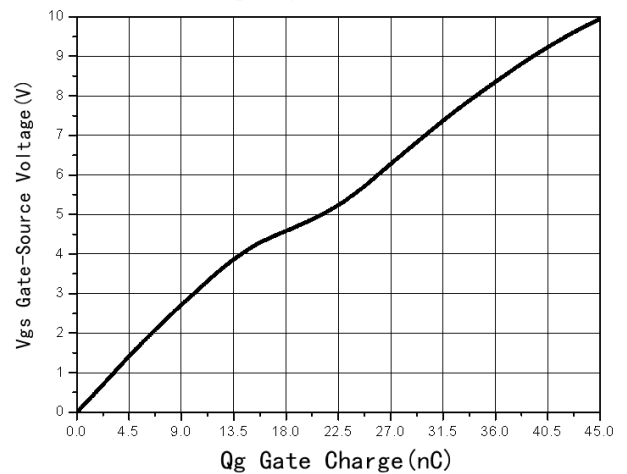


Fig6 Gate Charge

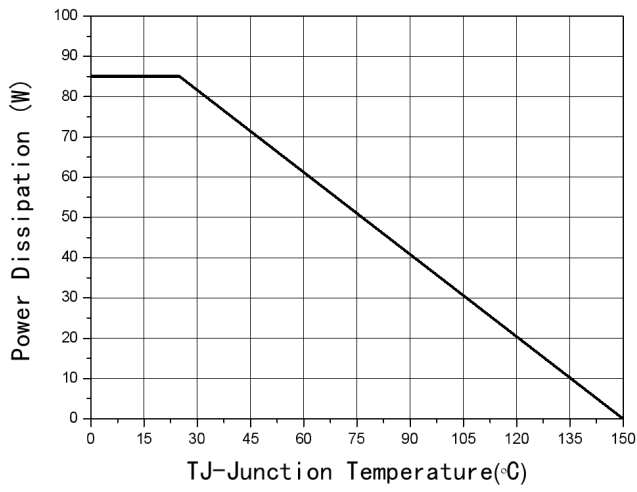


Fig7 Power De-rating

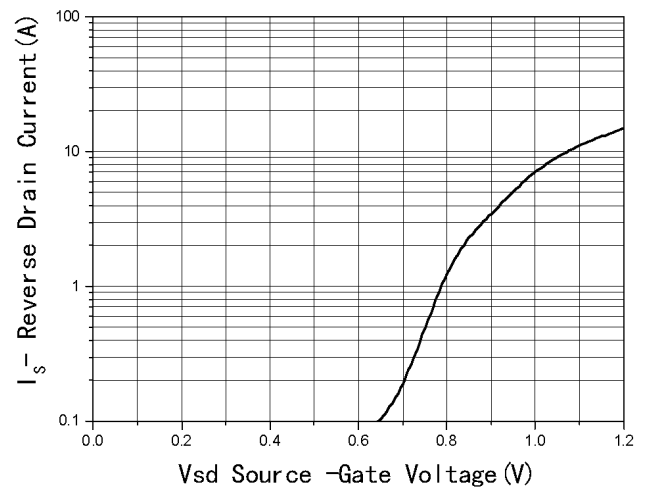
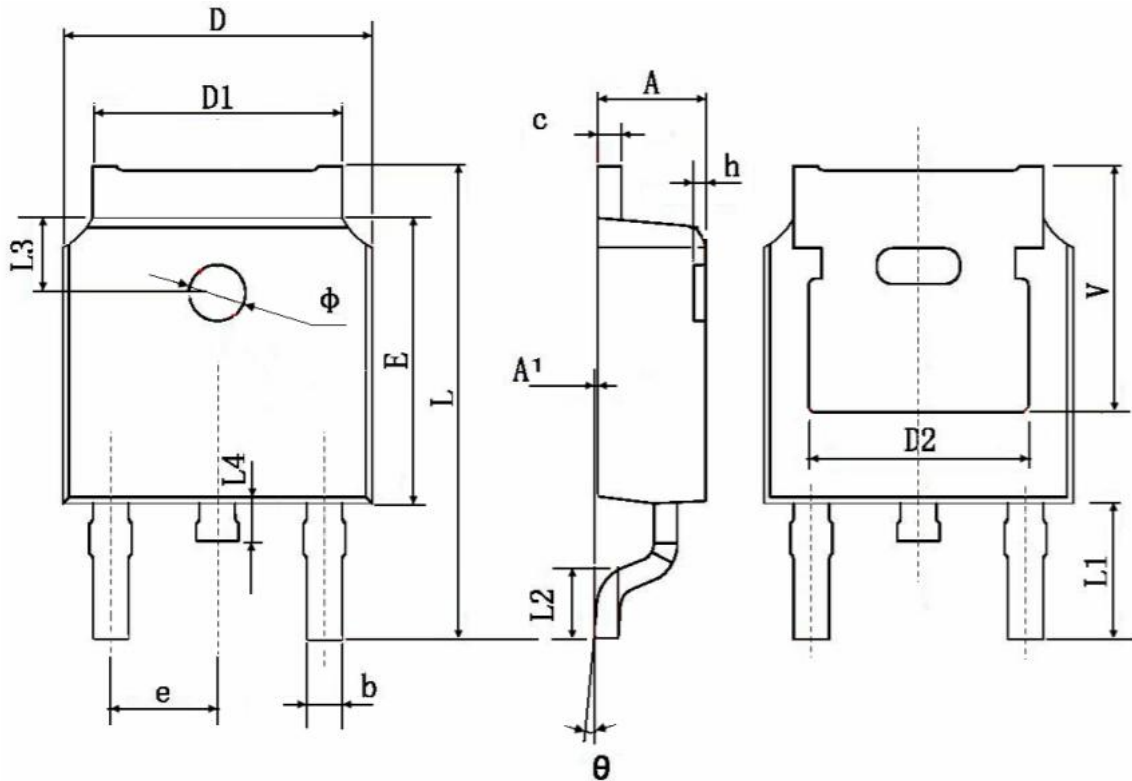


Fig8 Source-Drain Diode Forward

Package Information

- TO-252-2L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	